

A novel route to EUV resists design: Fundamental understanding of chemical processes

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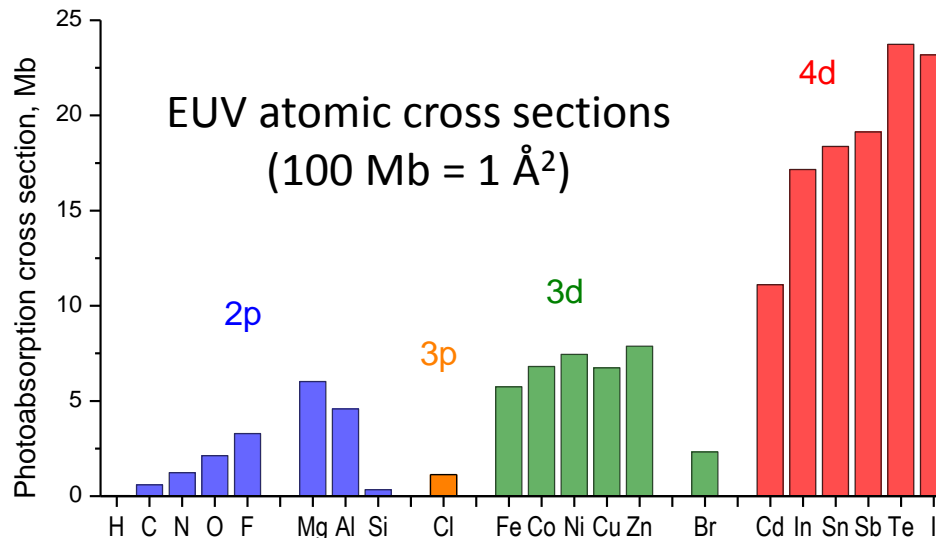
Motivation

- Increase sensitivity of EUV resist

$$30 \text{ mJ/cm}^2 = 20 \text{ photons/nm}^2$$

Table 1 Extreme Ultraviolet Absorption of Selected Materials

Material	Formula	Extreme Ultraviolet Absorption (50 nm film) (%)
Polypropylene	C ₃ H ₆	11
Poly(methyl methacrylate)	C ₅ H ₈ O ₂	24
Polyimide	C ₂₂ H ₁₀ N ₂ O ₅	25
Teflon	C ₂ F ₄	60
Hafnium oxide	HfO ₂	30
Tin oxide	SnO ₂	62

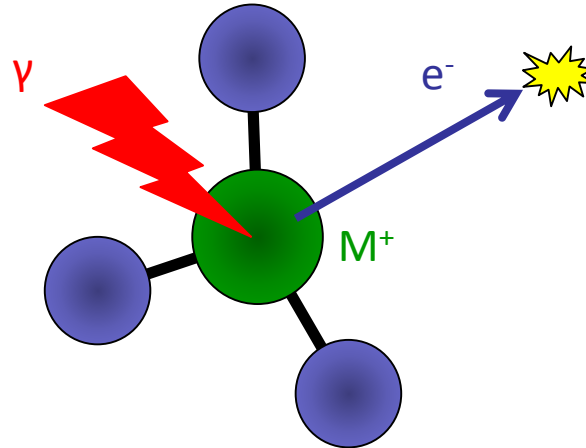


Processes After EUV Photon Absorption

- Gain fundamental understanding

Step 1

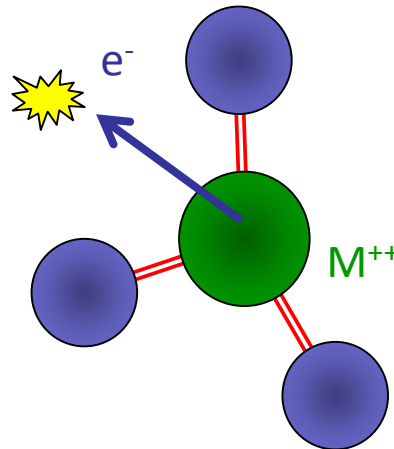
Photoionization



Step 2

Electronic Relaxation

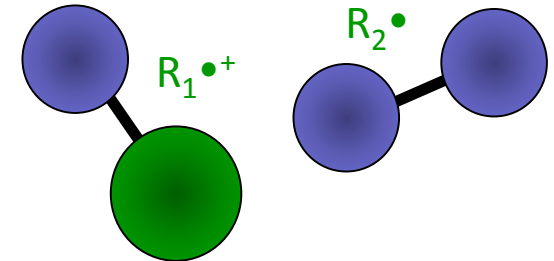
Auger process ?



Step 3

Atomic Relaxation

Fragmentation?



Our Approach

Gas-phase
single molecule



Condensed material

Step 1 Photoionization



Step 2 Electronic Relaxation

Auger process ?



Step 3 Atomic Relaxation

Fragmentation?



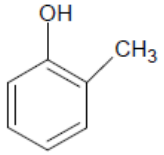
Photoelectron spectroscopy:

1. Electron kinetic energies
2. Electron yield

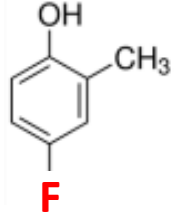
Mass spectrometry:

1. Fragmentation pattern after EUV photon absorption

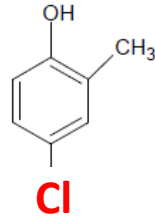
Samples



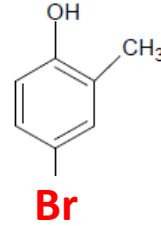
2-methylphenol



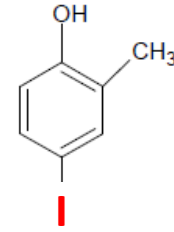
4-F-2-methylphenol



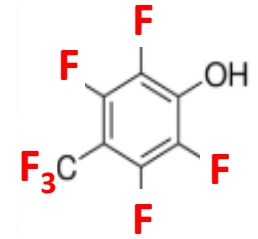
4-Cl-2-methylphenol



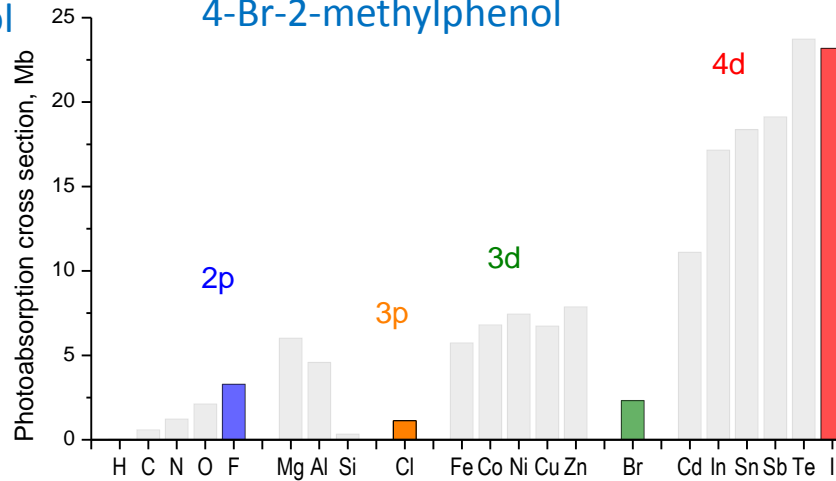
4-Br-2-methylphenol



4-I-2-methylphenol

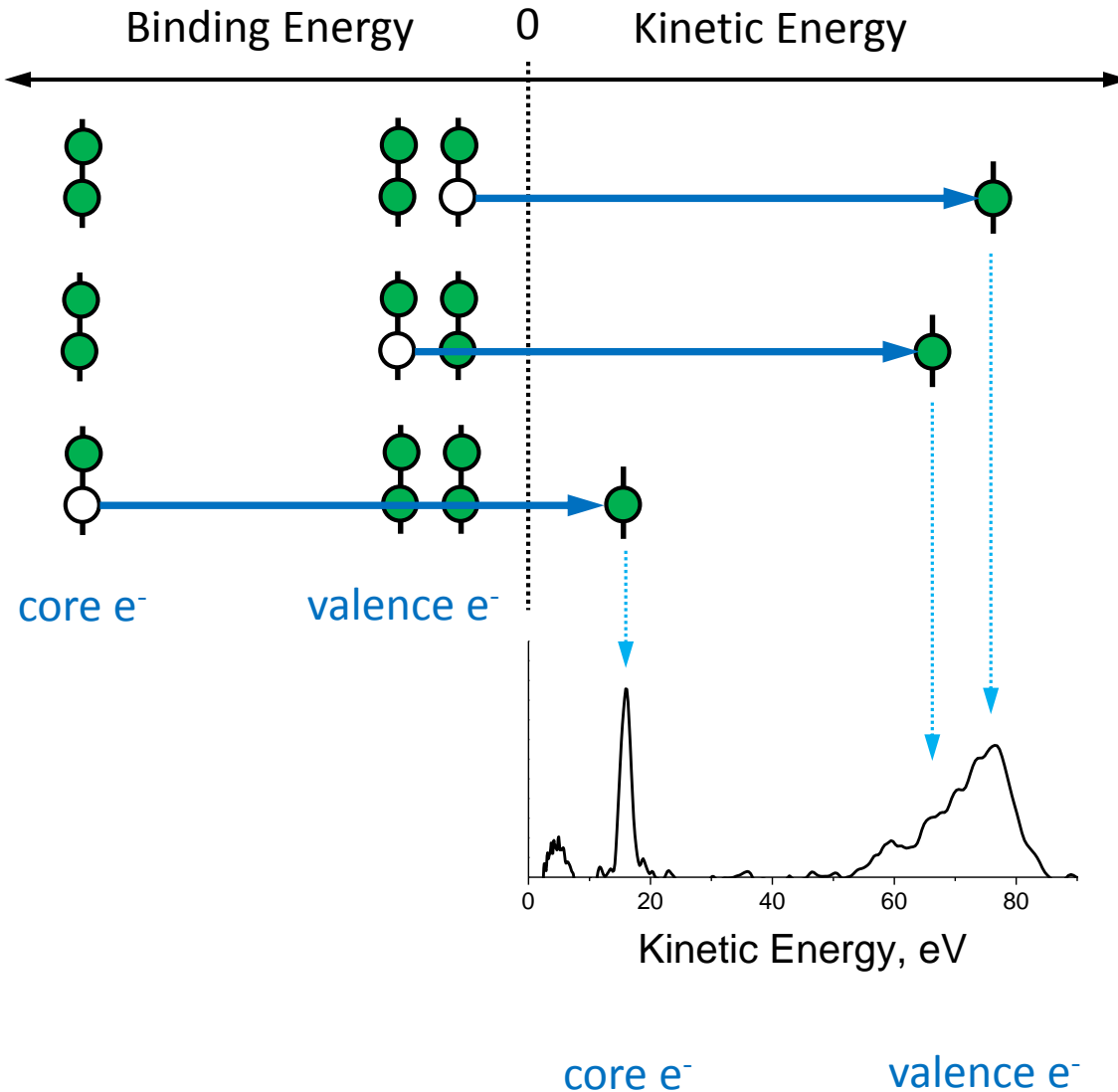


2,3,5,6-Tetrafluoro-4-(trifluoromethyl)phenol



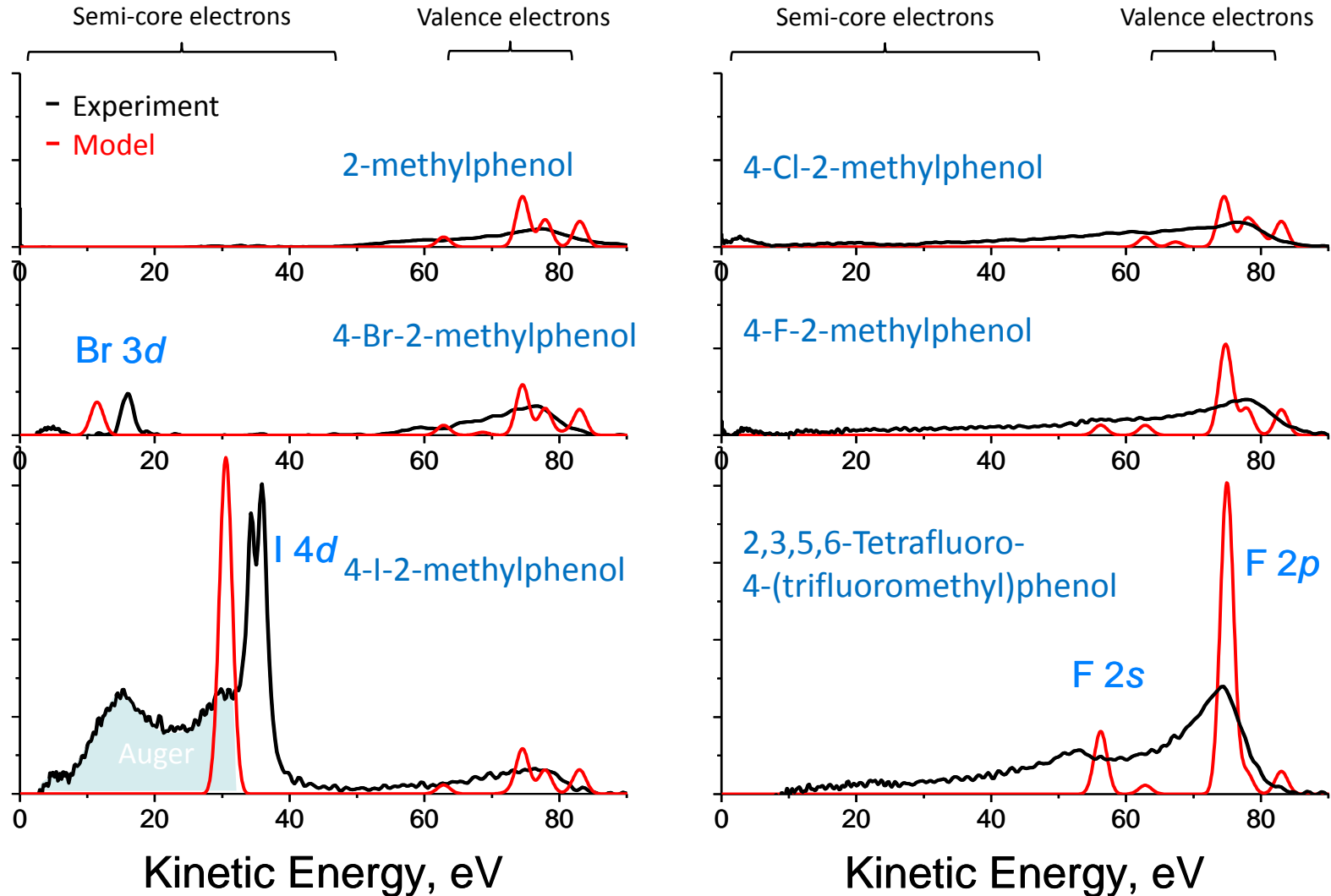
Compound	Absorbed EUV photons (50nm), %
2-Methylphenol	18
4-F-2-Methylphenol	25
4-Cl-2-Methylphenol	19
4-Br-2-Methylphenol	20
4-I-2-Methylphenol	51
2,3,5,6-tetra fluoro-4-(trifluoromethyl)phenol	48

Photoelectron Spectroscopy

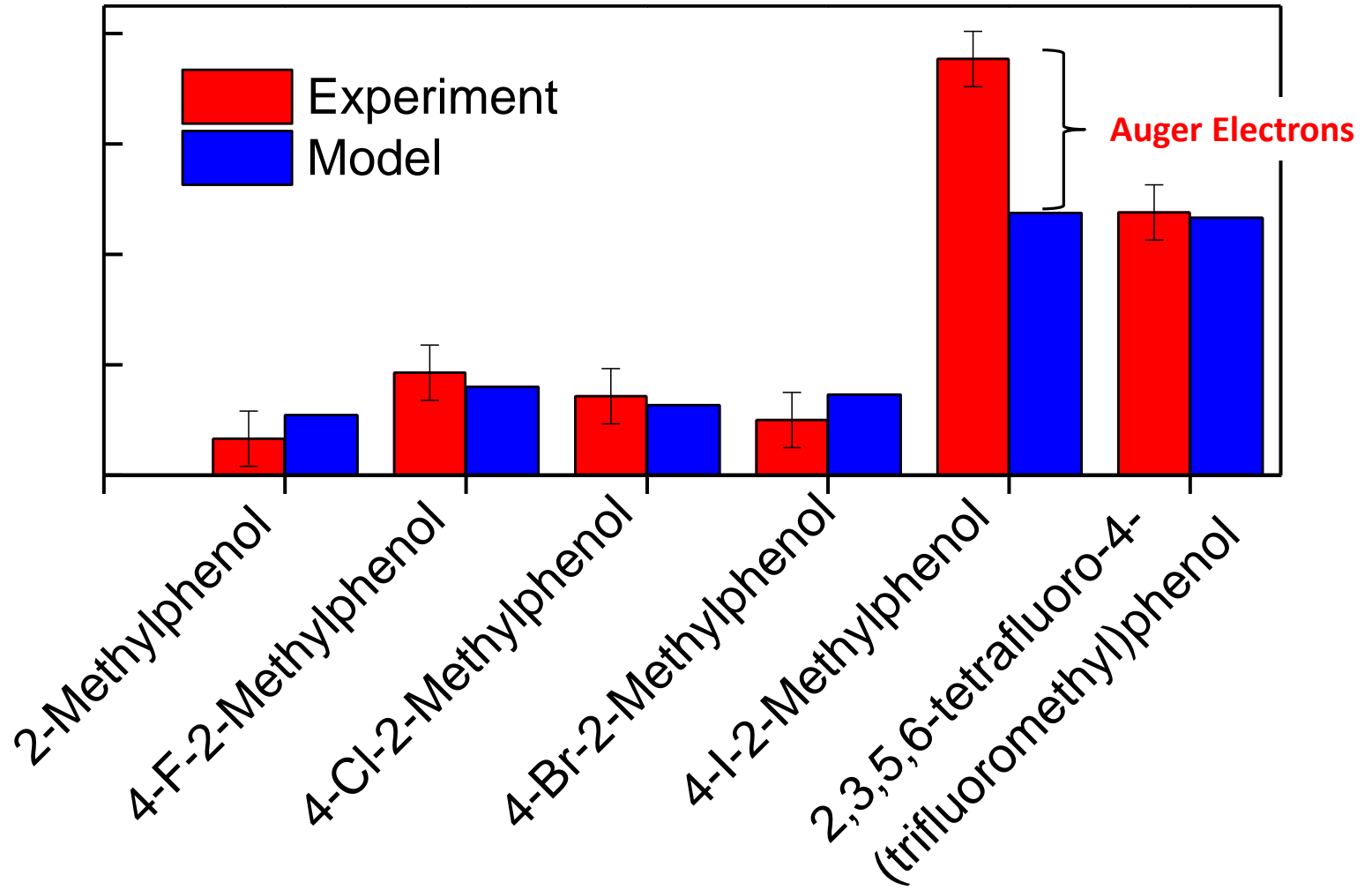


Photoelectron Spectroscopy

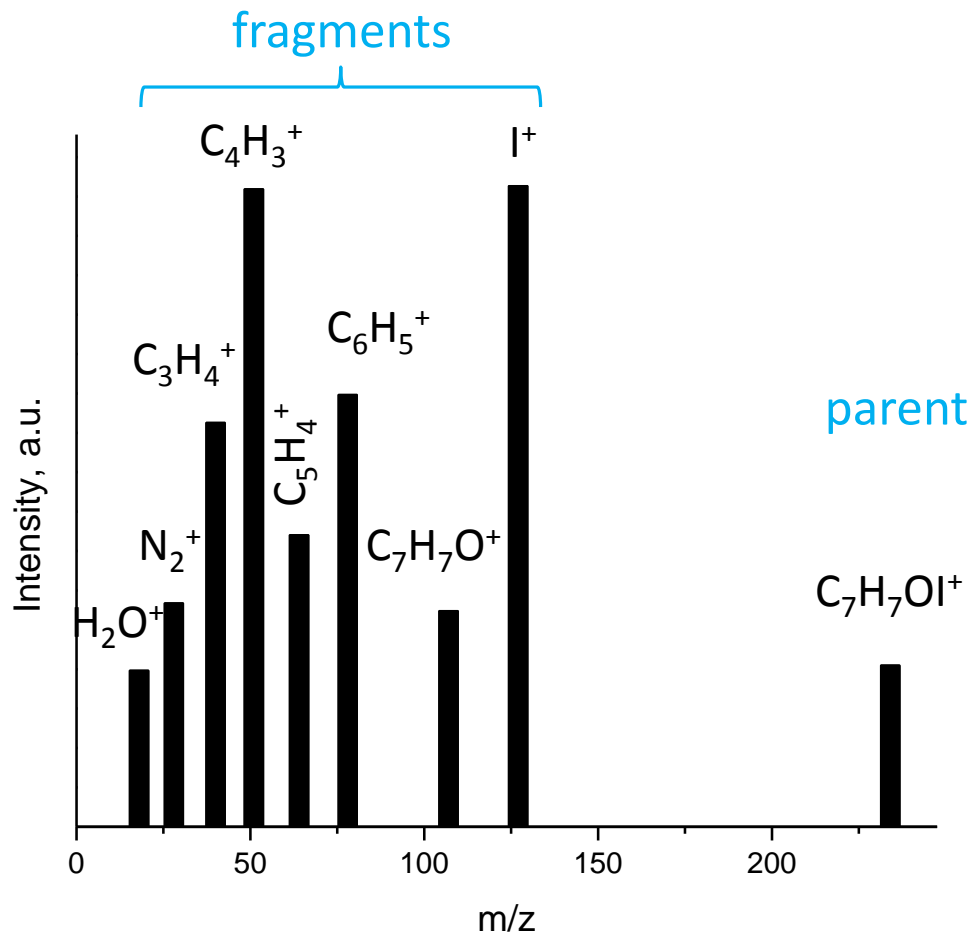
Step 1-2. Electron kinetic energies



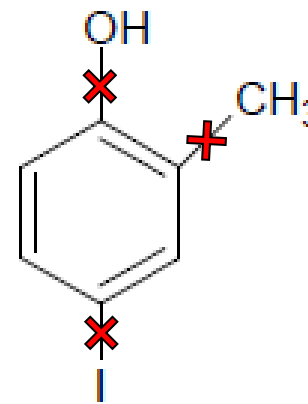
Relative Electron Yield



Step 3. Atomic relaxation

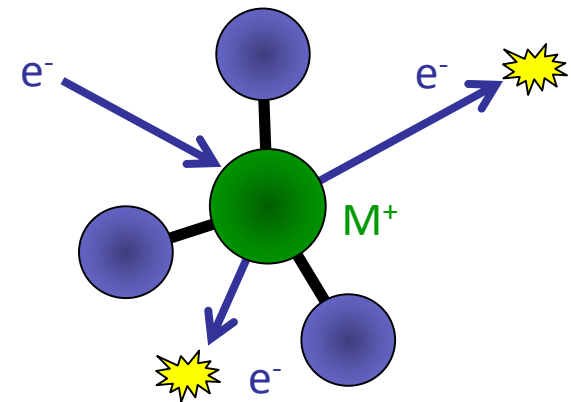


4-I-2-methylphenol



Condensed Resist?

- Photoabsorption, photoemission and Auger relaxation processes are almost unchanged
 - dielectric environment reduces binding energies ~ 4 eV
 - sharp lines are broadened
- Molecular fragmentation changes
 - fragments are trapped in polymer matrix, may recombine or generate secondary reactions...
- Inelastic electron scattering
 - electrons interact with molecules



Step 4 Inelastic Scattering



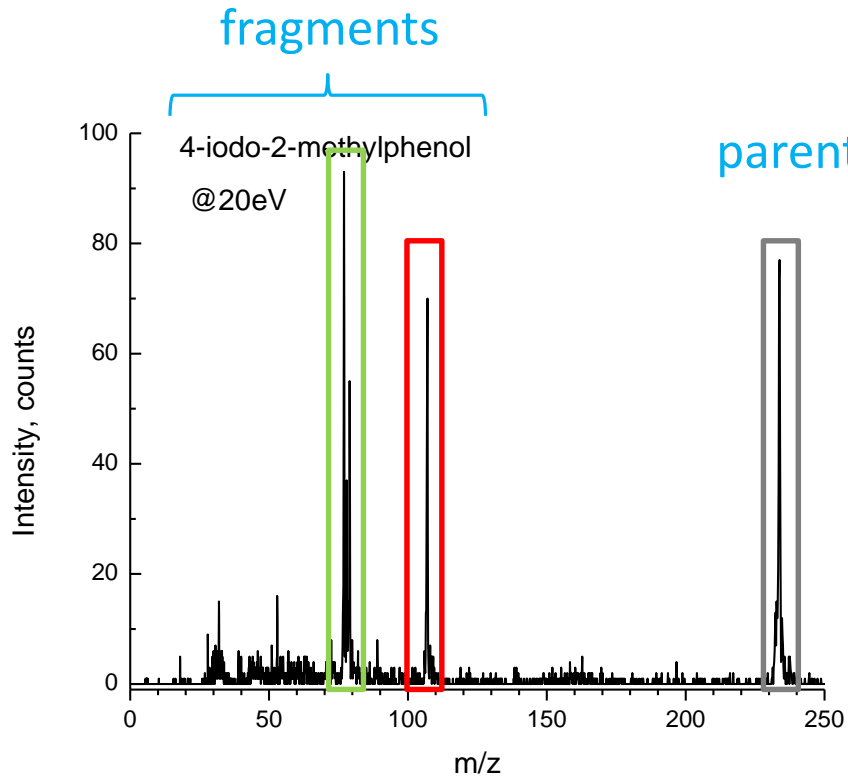
and more steps...

Mass spectrometry:

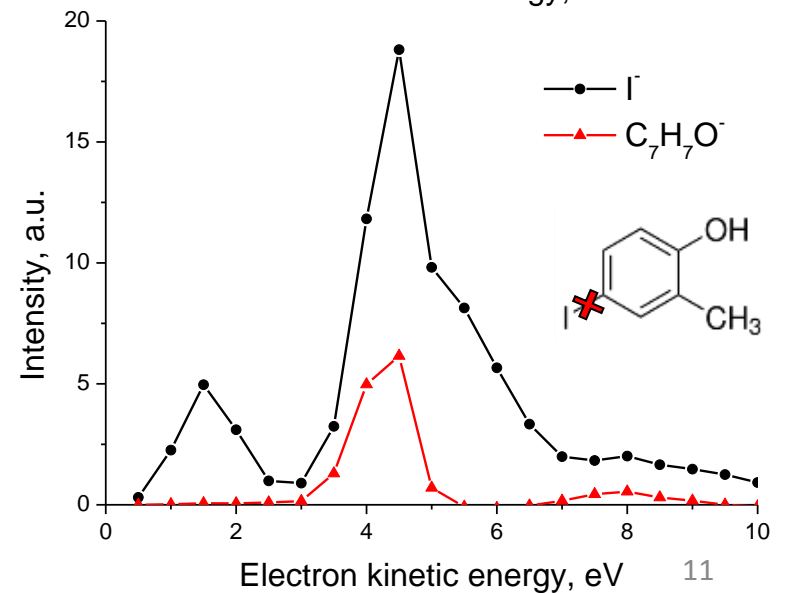
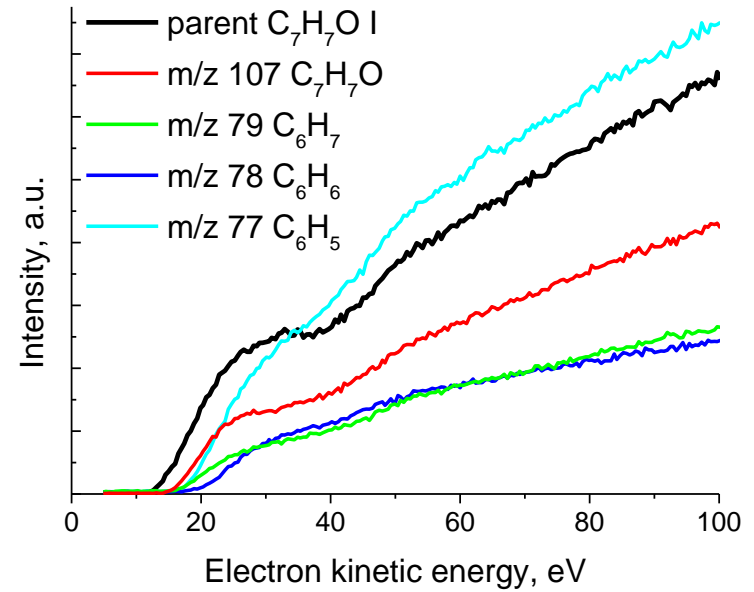
1. Fragmentation pattern after e^- collision

Mass Spectrometry: Electrons

Step 4. Inelastically scattered electrons



Low energy electrons:
dissociative electron attachment

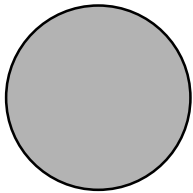


How to Study Condensed Resist

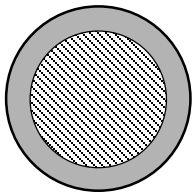
Gas-phase single molecule \Rightarrow Condensed resist

Nanoparticles:

uniform

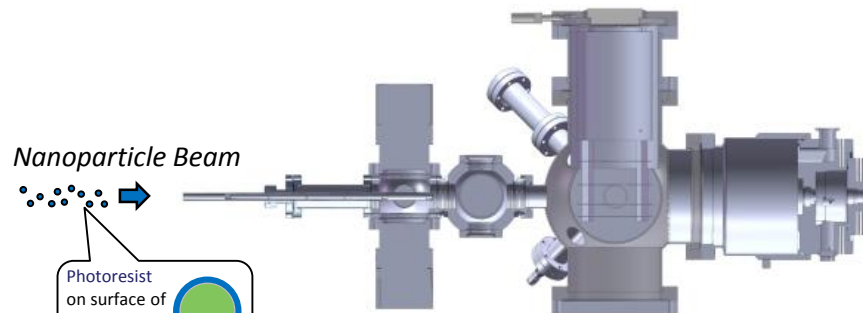
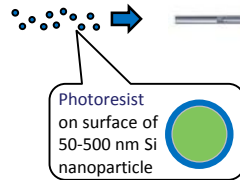


core-shell

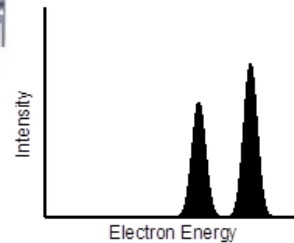
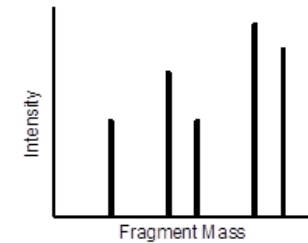


50-500nm

Nanoparticle Beam



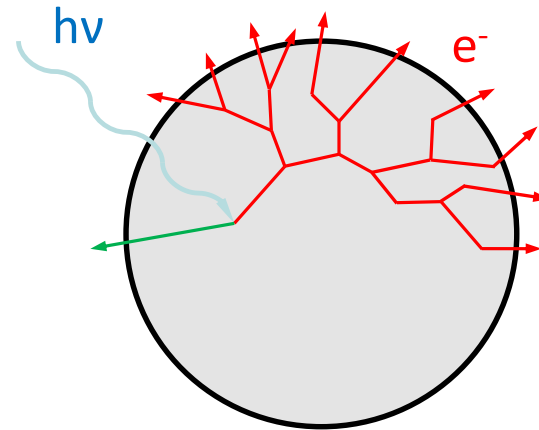
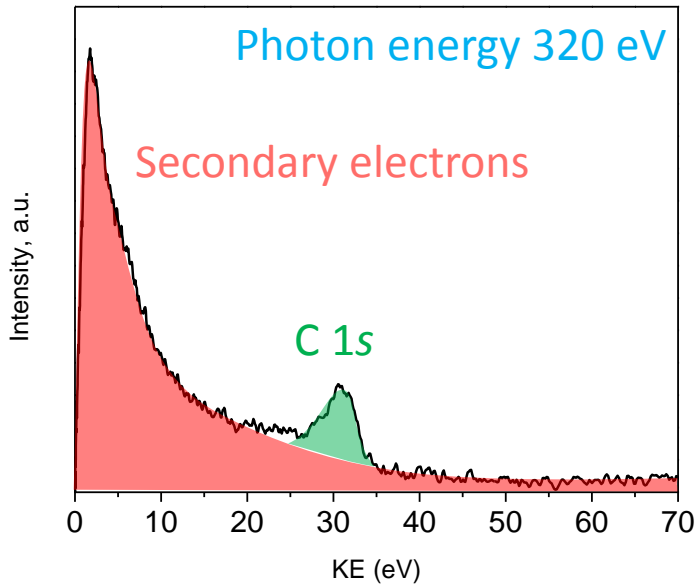
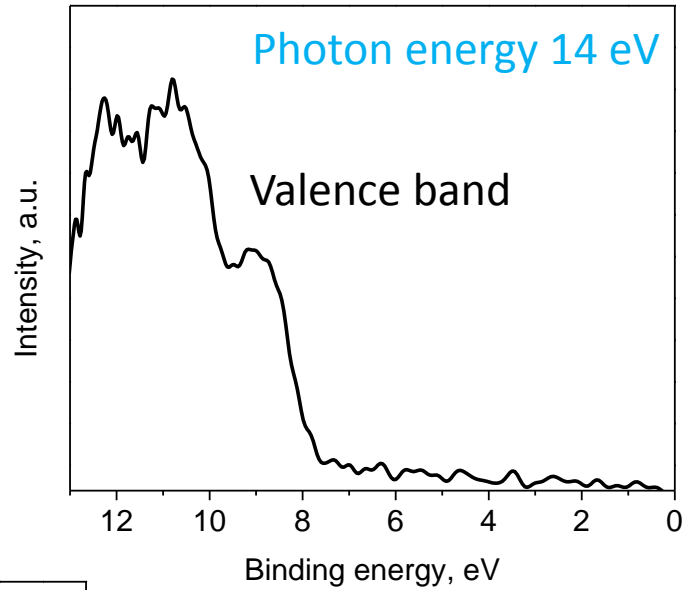
TOF-MS for chemical characterization of desorbed species



Velocity map imaging (VMI) for photoelectron energies and angular distributions

Photoelectron Spectra of Condensed Resist

E-beam resist:
4-Methyl-1-Acetoxycalixarene

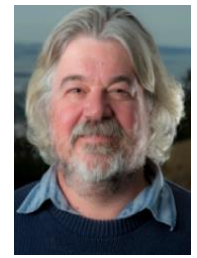


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Collaborative Team and Instrumentation is the Nat'l Lab Strength

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